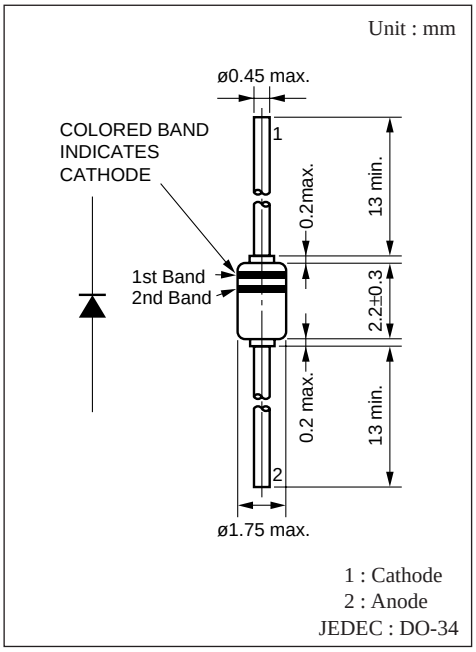
MA776

Silicon epitaxial planer type

For the switching circuit



■ Features

- Sealed in small glass package (DO-34)
- 5mm pitch insertion possible
- Low forward rise voltage V_F and satisfactory wave detection efficiency
- Temperature coefficient of forward characteristic is small.
- Extremely low reverse current I_R
- V_R (DC value)= 40V guaranteed

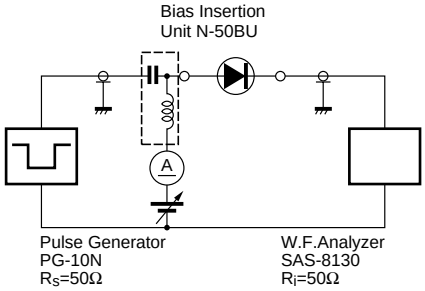
■ Absolute Maximum Ratings (Ta= 25˚C)

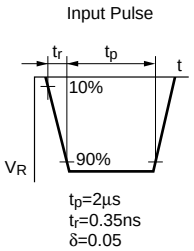
Parameter	Symbol	Rating	Unit
Reverse voltage (DC)	V_R	40	V
Repetitive peak reverse voltage	V_{RRM}	40	V
Peak forward current	I_{FM}	150	mA
Average forward current	I_F	30	mA
Junction temperature	T_j	125	˚C
Storage temperature	T_{stg}	– 55 to +125	˚C

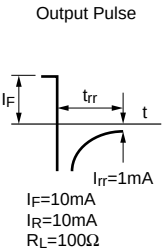
■ Electrical Characteristics (Ta= 25˚C)

Parameter	Symbol	Condition	min	typ	max	Unit
Reverse current (DC)	I_R	V_R= 40V			200	nA
Forward voltage (DC)	V_{F1}	I_F=1mA			0.4	V
	V_{F2}	I_F= 30mA			1	V
Terminal capacitance	C_t	V_R = 1V, f=1MHz		1.3		pF
Reverse recovery time	t_{rr}*	I_F = I_R=100mA I_{rr}= 1mA , R_L=100Ω		2		ns
Detection efficiency	η	V_{in}= 3$V_{(peak)}$, f= 30MHz R_L= 3.9kΩ, C_L=10pF		60		%

Note 1. Schottky barrier diode is sensitive to electric shock (static electricity, etc.). Due attention must be paid on charge of a human body and leakage from the equipment used.
2. Rated input/output frequency : 2000MHz
3. * t_{rr} measuring circuit



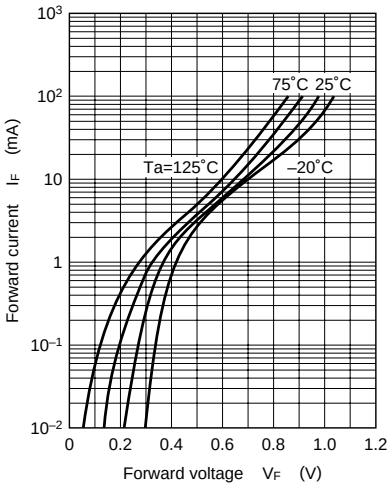




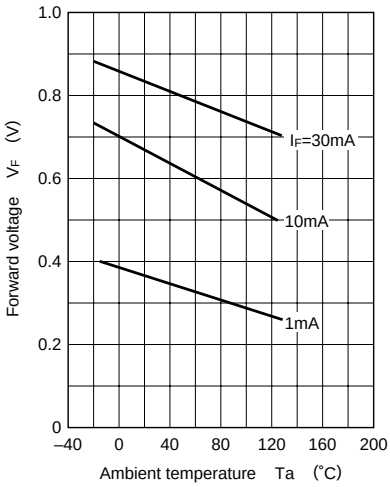
■ Cathode Indication

Type No.		MA776
Color	1st Band	Silver
	2nd Band	Yellow

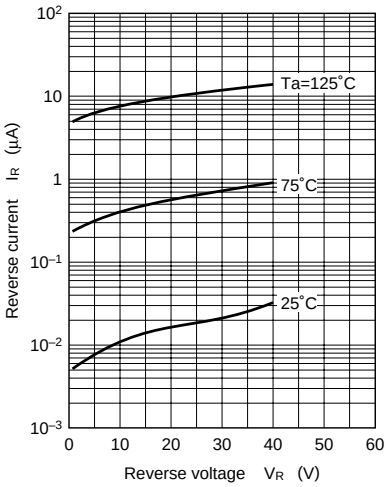
$I_F - V_F$



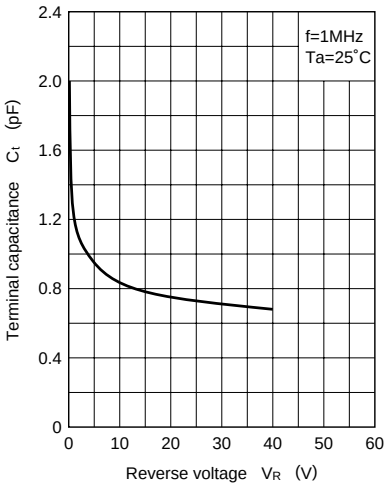
$V_F - Ta$



$I_R - V_R$



$C_t - V_R$



$I_R - Ta$